

AUG 30 2007

Application Number 10/824942
Response to Office Action dated 03/30/2007 and
Response to Notice of Non-Compliant RCE dated 08/13/2007

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently Amended) A semiconductor integrated circuit device, comprising
a digital circuit part and an analog circuit part that are disposed on a surface of
one semiconductor substrate,
wherein a dummy layer part made of polysilicon that is the same as polysilicon
composing a gate of a transistor is disposed directly on a portion of the semiconductor
substrate being of higher resistance than a well region in the circuit parts of the
semiconductor substrate between the digital circuit part and the analog circuit part, and
a dummy diffused region is provided between an area under the dummy layer part
and one of the digital circuit part and the analog circuit part, with a power-supply
potential being applied to the dummy diffused region so as to be capable of supplying a
collector current of a parasitic transistor formed with the semiconductor substrate with a
base and well regions of the digital and analog circuit parts as an emitter and a collector,
respectively.

2-4. (Canceled)

5. (Currently Amended) A camera, comprising:
an imaging element; and
a semiconductor integrated circuit device comprising a digital circuit part for
driving the imaging element and an analog circuit part for analog processing an image
detecting signal output from the imaging element,
wherein the semiconductor integrated circuit device has a structure in which a
dummy layer part made of polysilicon that is the same as polysilicon composing a gate of

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a transistor is disposed directly on a portion of the semiconductor substrate being of higher resistance than a well region in the circuit part of the semiconductor substrate between the digital circuit part and the analog circuit part, and

a dummy diffused region is provided between an area under the dummy layer part and one of the digital circuit part and the analog circuit part, with a power-supply potential being applied to the dummy diffused region so as to be capable of supplying a collector current of a parasitic transistor formed with the semiconductor substrate as a base and well regions of the digital and analog circuit parts as an emitter and a collector, respectively.

6. (Canceled)